

| VRRM | IF (TC≤135°C) | QC |
|------|----------------|------|
| 650V | 15A | 30nC |

Applications:

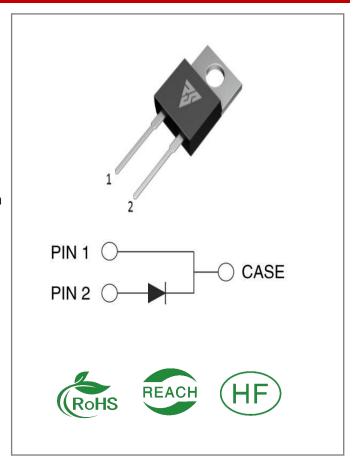
- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses



Ordering Information

| Part Number | Package | Marking | Packing | Qty. |
|-------------|----------|-----------|---------|--------|
| RSS10065A | TO-220-2 | RSS10065A | Tube | 50 PCS |



Maximum Ratings (TJ= 25°C unless otherwise specified)

| Symbo I | Parameter | Valu e | Unit | Test Conditions | Not e |
|-------------|---|------------------|------------------------|---|-----------|
| VRRM | Repetitive Peak Reverse Voltage | 650 | V | TC = 25°C | |
| VRSM | Surge Peak Reverse Voltage | 650 | V | TC = 25°C | |
| VR | DC Blocking Voltage | 650 | V | TC = 25°C | |
| IF | Forward Current | 32 15 10 | А | TC ≤ 25°C TC ≤ 135°C TC ≤ 154°C | Fig. |
| IFSM | Non-Repetitive Forward Surge Current | 96 83 | А | TC = 25° C, tp = 10ms, Half Sine Wave TC = 110° C, tp = 10ms, Half Sine Wave | |
| IFRM | Repetitive Peak Forward Surge Current | 85 | Α | TC = 25°C, tp = 10ms, Half Sine Wave | |
| Ptot | Power Dissipation | 127 | W | TC = 25℃ | Fig. 4 |
| TC | Maximum Case Temperature | 154 | $^{\circ}$ | | |
| TJ,TST G | Operating Junction and Storage Temperature | -55 to17 5 | $^{\circ}\!\mathbb{C}$ | | |

Electrical Characteristics (TJ= 25 °C unless otherwise specified)

| Symbo I | Parameter | Тур. | Max · | Unit | Test Conditions | Note |
|------------|------------------------------|-----------------|----------|------|--|-------|
| VF | Forward Voltage | 1.37 1.66 | 1.6 - | ٧ | IF = 10A, TJ = 25°C IF = 10A, TJ = 175°C | Fig.1 |
| IR | Reverse Current | 5 12 | 60 - | μΑ | VR = 650V, TJ = 25°C VR = 650V, TJ = 175°C | Fig.2 |
| С | Total Capacitance | 455 57 56 | / | pF | VR = 1V, TJ = 25° C, f = 1MHz VR = 200V, TJ = 25° C, f = 1MHz VR = 400V, TJ = 25° C, f = 1MHz | Fig.5 |
| QC | Total Capacitive Charge | 30 | / | nC | VR =400V, | Fig.6 |
| Ec | Capacitance Stored Energy | 4.8 | | uJ | VR =400V, | Fig.7 |

Thermal Characteristics (TJ= 25 ℃ unless otherwise specified)

| Symbol | Parameter | Тур. | Unit | Note |
|--------|--|-------|------|-------|
| RθJC | Thermal Resistance from Junction to Case | 1.175 | °C/W | Fig.8 |



Typical Feature Curve

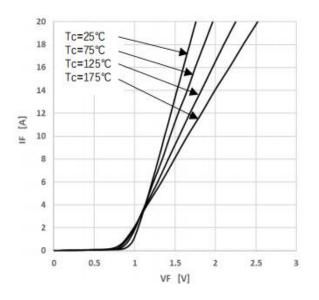


Figure 1 Forward Characteristics

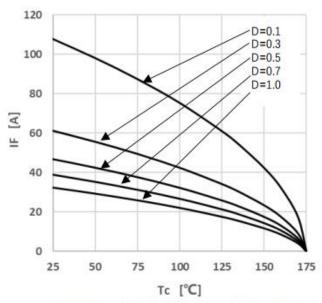


Figure 3 Peak Forward Current Derating

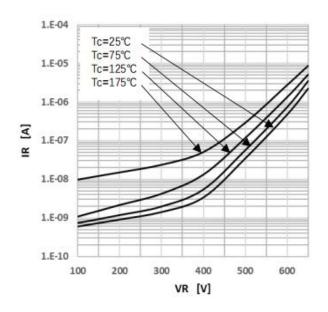


Figure 2 Reverse Characteristics

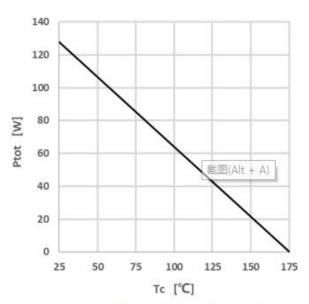


Figure 4 Power Dissipation



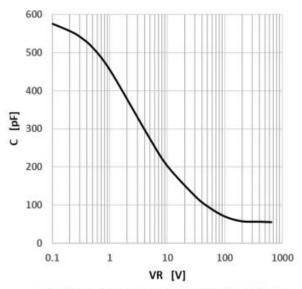


Figure 5 Capacitance vs. Reverse Voltage

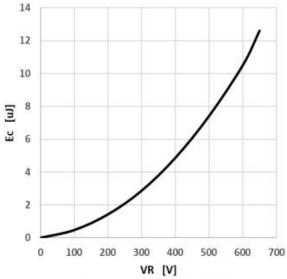


Figure 7 Capacitance Stored Energy

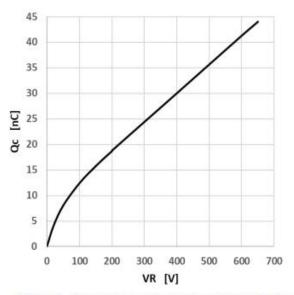


Figure 6 Capacitance Charge vs. Reverse Voltage

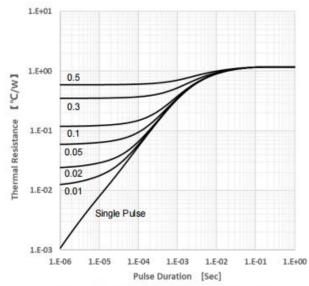
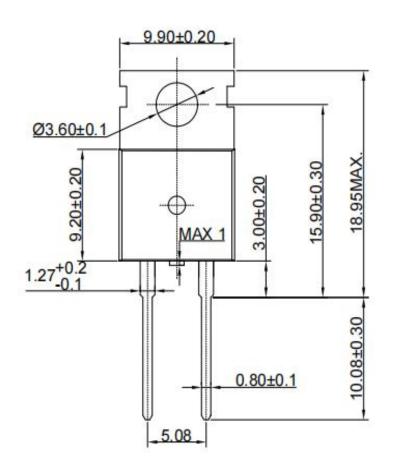


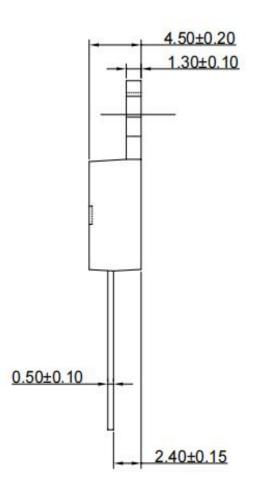
Figure 8 Transient Thermal Impedance

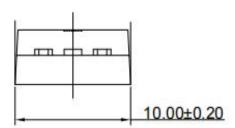
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Package outline drawing(TO-220 Unit: mm)









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